



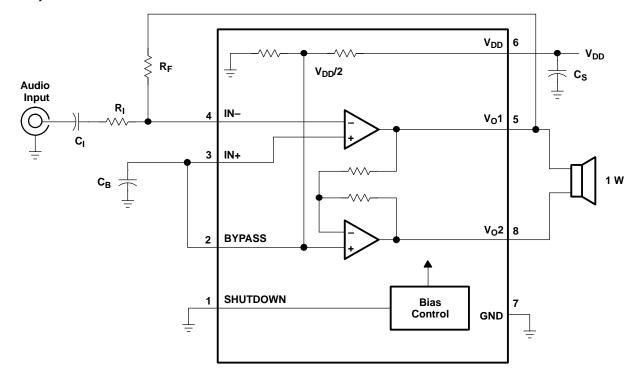
1-W MONO AUDIO POWER AMPLIFIER

FEATURES

- 1-W BTL Output (5 V, 0.11 % THD+N)
- 3.3-V and 5-V Operation
- No Output Coupling Capacitors Required
- Shutdown Control ($I_{DD} = 0.6 \mu A$)
- Uncompensated Gains of 2 to 20 (BTL Mode)
- Surface-Mount Packaging
- Thermal and Short-Circuit Protection
- High Supply Ripple Rejection Ratio (56 dB at 1 kHz)
- LM4861 Drop-In Compatible

DESCRIPTION

The TPA4861 is a bridge-tied load (BTL) audio power amplifier capable of delivering 1 W of continuous average power into an $8-\Omega$ load at 0.2% THD+N from a 5-V power supply in voiceband frequencies (f < 5 kHz). A BTL configuration eliminates the need for external coupling capacitors on the output in most applications. Gain is externally configured by means of two resistors and does not require compensation for settings of 2 to 20. Features of the amplifier are a shutdown function for power-sensitive applications as well as internal thermal and short-circuit protection. The TPA4861 works seamlessly with TI's TPA4860 in stereo applications. The amplifier is available in an 8-pin SOIC surface-mount package that reduces board space and facilitates automated assembly.





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

AVAILABLE OPTIONS

т.	PACKAGED DEVICE	
'A	SMALL OUTLINE ⁽¹⁾ (D)	
−40°C to 85°C	TPA4861D	

(1) The D package is available tape and reeled. To order a tape and reeled part, add the suffix R to the part number (e.g., TPA4861DR).

Terminal Functions

TERMINA	TERMINAL		DESCRIPTION
NAME	NO.	I/O	DESCRIPTION
BYPASS	2	I	BYPASS is the tap to the voltage divider for internal mid-supply bias. This terminal should be connected to a 0.1 - μ F $- 1.0$ - μ F capacitor when used as an audio power amplifier.
GND	7		GND is the ground connection.
IN-	4	ı	IN- is the inverting input. IN- is typically used as the audio input terminal.
IN+	3	ı	IN+ is the noninverting input. IN+ is typically tied to the BYPASS terminal.
SHUTDOWN	1	ı	SHUTDOWN places the entire device in shutdown mode when held high ($I_{DD} \sim 0.6 \mu A$).
V _O 1	5	0	V _O 1 is the positive BTL output.
V _O 2	8	0	V _O 2 is the negative BTL output.
V_{DD}	6		V _{DD} is the supply voltage terminal.

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range (unless otherwise noted)(1)

		UNIT
V_{DD}	Supply voltage	6 V
V _I	Input voltage	–0.3 V to V _{DD} +0.3 V
	Continuous total power dissipation	Internally Limited (see Dissipation Rating Table)
T _A	Operating free-air temperature range	-40°C to 85°C
TJ	Operating junction temperature range	−40°C to 150°C
T _{stg}	Storage temperature range	−65°C to 150°C
	Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

DISSIPATION RATING TABLE

PACKAGE	$T_A \le 25^{\circ}C$	DERATING FACTOR	T _A = 70°C	T _A = 85°C
D	725 mW	5.8 mW/°C	464 mW	377 mW

RECOMMENDED OPERATING CONDITIONS

			MIN	MAX	UNIT
V_{DD}	Supply voltage		2.7	5.5	V
	V Common made insult valtage	V _{DD} = 3 V	1.25	2.7	V
V _{IC}	Common-mode input voltage	V _{DD} = 5 V	1.25	4.5	V
T _A	Operating free-air temperature		-40	85	°C



ELECTRICAL CHARACTERISTICS

at specified free-air temperature, V_{DD} = 3.3 V (unless otherwise noted)

PARAMETER TEST CONDITIONS		TPA4861			UNIT	
	PARAMETER	MIN TYP MA		MAX	ONT	
V _{oo}	Output offset voltage	See ⁽¹⁾			20	mV
PSRR	Power supply rejection ratio $(\Delta V_{DD}/\Delta V_{OO})$	V _{DD} = 3.2 V to 3.4 V		75		dB
I _{DD}	Supply current			2.5		mA
I _{DD(SD)}	Supply current, shutdown			0.6		μΑ

⁽¹⁾ At 3 V < V_{DD} < 5 V the dc output voltage is approximately $V_{DD}/2$.

OPERATING CHARACTERISTICS

 V_{DD} = 3.3 V, T_A = 25°C, R_L = 8 Ω

	PARAMETER		TEST COND			PA486	1	UNIT
	PARAMETER		TEST CONDITIONS MIN TYP MA		MAX			
В	Po Output power ⁽¹⁾		THD = 0.2%, f = 1 kHz,	$A_V = -2 \text{ V/V}$		400		mW
[0			THD = 2%, f = 1 kHz,	$A_V = -2 \text{ V/V}$		500		mW
B _{OM}	B _{OM} Maximum output power bandwidth		Gain = -10 V/V,	THD = 2%		20		kHz
B ₁	Unity-gain bandwidth		Open Loop			1.5		MHz
	Cumply ripple rejection ratio	BTL	f = 1 kHz,	C _B = 0.1 μF		56		dB
	Supply ripple rejection ratio SE		f = 1 kHz,	C _B = 0.1 μF		30		dB
V _n	Noise output voltage (2)		Gain = -2 V/V			20		μV

⁽¹⁾ Output power is measured at the output terminals of the device.

ELECTRICAL CHARACTERISTICS

at specified free-air temperature range, $V_{DD} = 5 \text{ V}$ (unless otherwise noted)

PARAMETER TEST CONDITION		Т	PA486	LINUT		
	PARAMETER	TEST CONDITION MIN TYP MA		MAX	UNIT	
V _{oo}	Output offset voltage	See (1)			20	mV
PSRR	Power supply rejection ratio ($\Delta V_{DD}/\Delta V_{OO}$)	V _{DD} = 4.9 V to 5.1 V		70		dB
I _{DD}	Supply current			3.5		mA
I _{DD(SD)}	Supply current, shutdown			0.6		μΑ

⁽¹⁾ At 3 V < V_{DD} < 5 V the dc output voltage is approximately $V_{DD}/2$.

OPERATING CHARACTERISTICS

 $V_{DD} = 5 \text{ V}, T_A = 25^{\circ}\text{C}, R_L = 8 \Omega$

	DADAMETED	DADAMETED		TEST CONDITIONS		TPA4861			
	PARAMETER		TEST CONDI	HONS	MIN	TYP	MAX	UNIT	
IPo Output power ⁽¹⁾		THD = 0.2%, f = 1 kHz,	A _V = -2 V/V		1000		mW		
		THD = 2%, f = 1 kHz,	$A_V = -2 \text{ V/V}$		1100		mW		
B _{OM}	B _{OM} Maximum output power bandwidth		Gain = -10 V/V,	THD = 2%		20		kHz	
B ₁	Unity-gain bandwidth		Open Loop			1.5		MHz	
	Cumply ripple rejection ratio	BTL	f = 1 kHz,	C _B = 0.1 μF	•	56		dB	
	Supply ripple rejection ratio S		f = 1 kHz,	$C_B = 0.1 \mu F$		30		dB	
V _n	Noise output voltage (2)		Gain = -2 V/V			20		μV	

⁽¹⁾ Output power is measured at the output terminals of the device.

⁽²⁾ Noise voltage is measured in a bandwidth of 20 Hz to 20 kHz.

⁽²⁾ Noise voltage is measured in a bandwidth of 20 Hz to 20 kHz.



TYPICAL CHARACTERISTICS

Table of Graphs

			FIGURE
V _{oo}	Output offset voltage	Distribution	1, 2
I _{DD}	Supply current distribution	vs Free-air temperature	3, 4
TUD.A	Total harmonia distantian plus paisa	vs Frequency	5, 6, 7, 8, 9, 10,11,15, 16,17,18
THD+N	Total harmonic distortion plus noise	vs Output power	12, 13, 14, 19,20,21
I _{DD}	Supply current	vs Supply voltage	22
V _n	Output noise voltage	vs Frequency	23, 24
	Maximum package power dissipation	vs Free-air temperature	25
	Power dissipation	vs Output power	26, 27
	Maximum output power	vs Free-air temperature	28
	Outract	vs Load resistance	29
	Output power	vs Supply voltage	30
	Open-loop gain	vs Frequency	31
k _{SVR}	Supply ripple rejection ratio	vs Frequency	32, 33

DISTRIBUTION OF TPS4861 OUTPUT OFFSET VOLTAGE

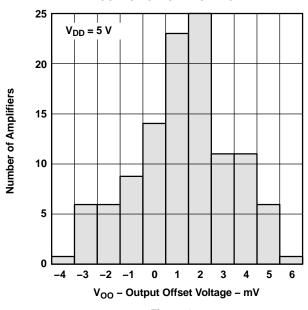


Figure 1.

DISTRIBUTION OF TPS4861 OUTPUT OFFSET VOLTAGE

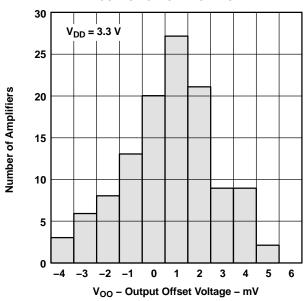


Figure 2.



SUPPLY CURRENT DISTRIBUTION VS FREE-AIR TEMPERATURE

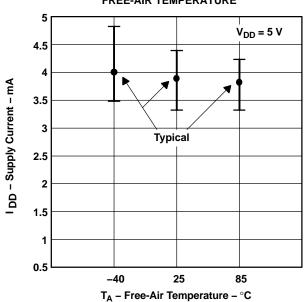
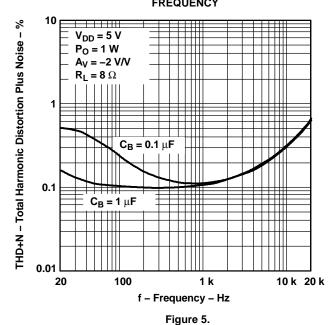


Figure 3.

TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY



SUPPLY CURRENT DISTRIBUTION
vs
FREE-AIR TEMPERATURE

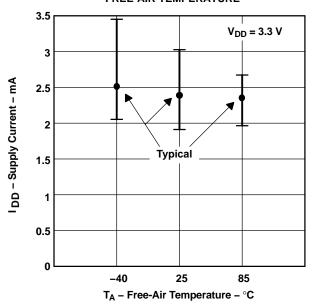


Figure 4.

TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY

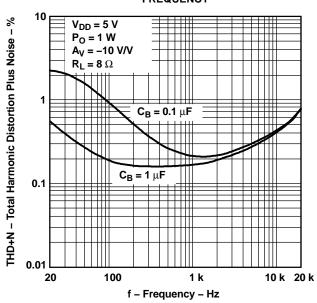


Figure 6.



TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY

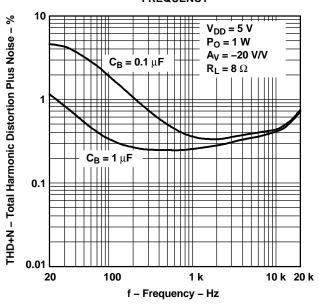


Figure 7.

TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY

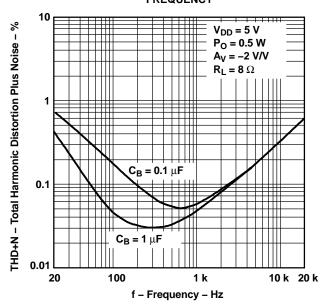
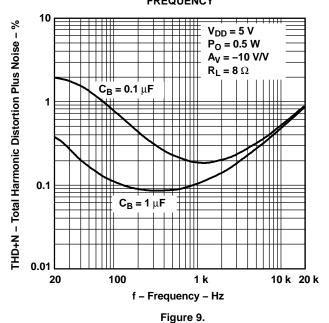


Figure 8.

TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY



TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY

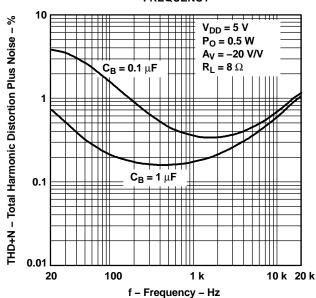


Figure 10.



TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY

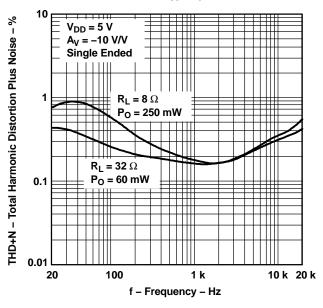


Figure 11.

TOTAL HARMONIC DISTORTION + NOISE vs OUTPUT POWER

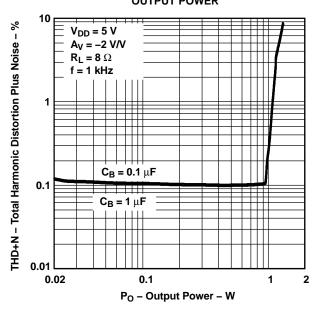


Figure 13.

TOTAL HARMONIC DISTORTION + NOISE vs OUTPUT POWER

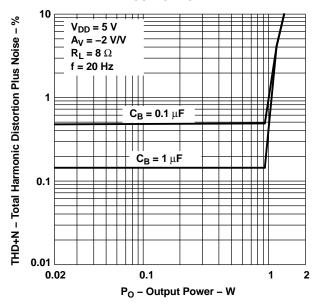


Figure 12.

TOTAL HARMONIC DISTORTION + NOISE vs OUTPUT POWER

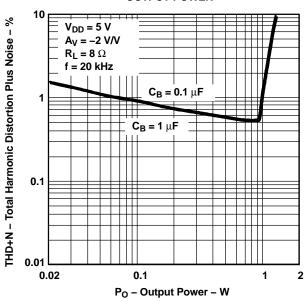


Figure 14.



TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY

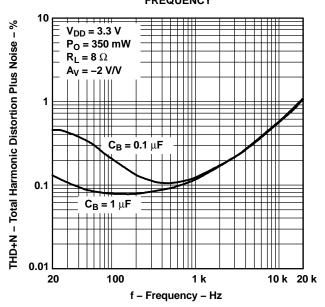


Figure 15.

FREQUENCY

TOTAL HARMONIC DISTORTION + NOISE

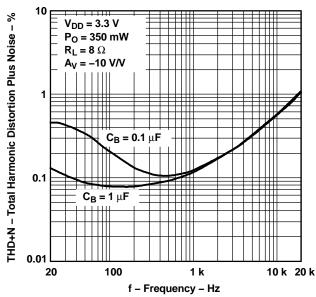
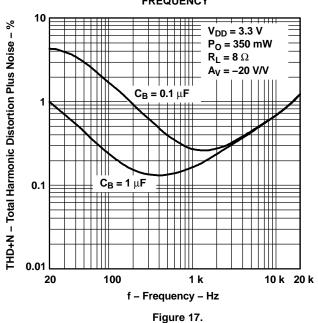


Figure 16.

TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY



TOTAL HARMONIC DISTORTION + NOISE vs FREQUENCY

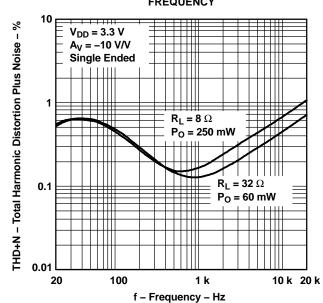
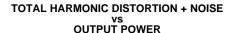
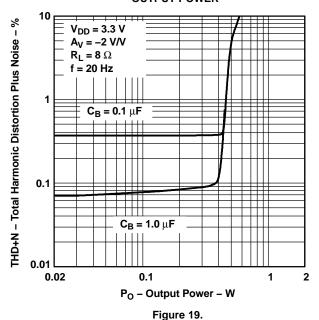


Figure 18.







TOTAL HARMONIC DISTORTION + NOISE vs OUTPUT POWER

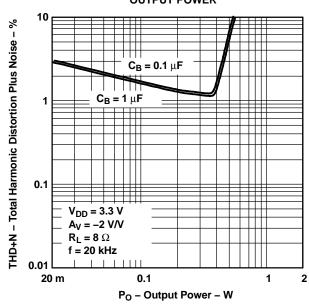
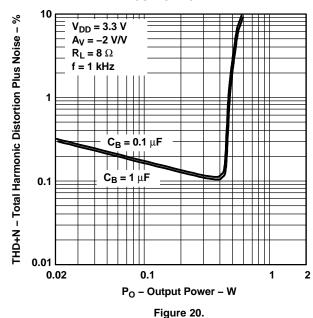


Figure 21.

TOTAL HARMONIC DISTORTION + NOISE vs OUTPUT POWER



SUPPLY CURRENT VS SUPPLY VOLTAGE

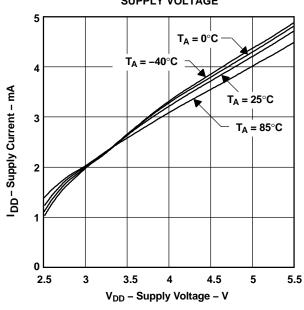
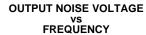


Figure 22.





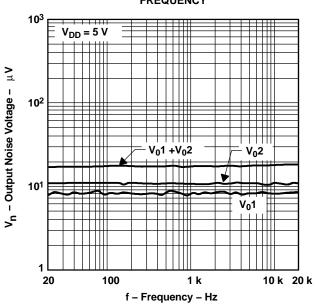


Figure 23.

OUTPUT NOISE VOLTAGE vs FREQUENCY

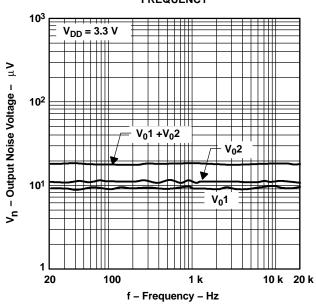


Figure 24.

MAXIMUM PACKAGE POWER DISSIPATION vs FREE-AIR TEMPERATURE

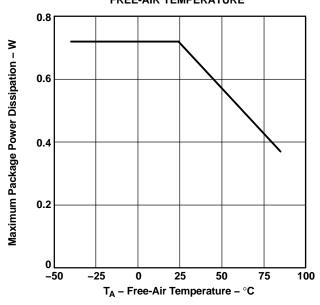


Figure 25.

POWER DISSIPATION vs OUTPUT POWER

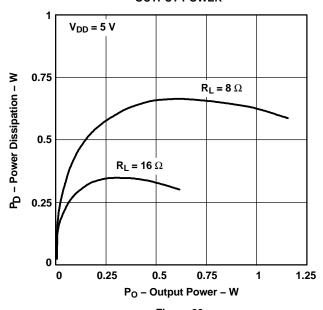
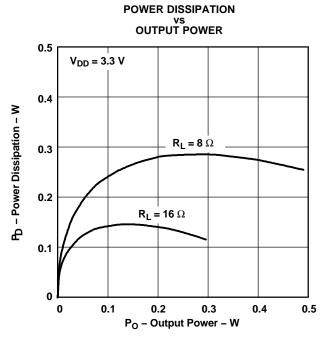


Figure 26.







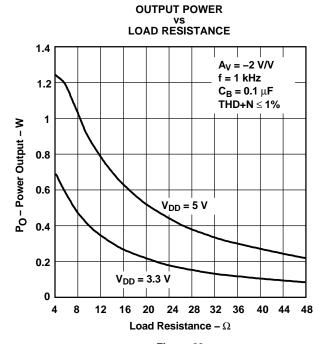


Figure 29.

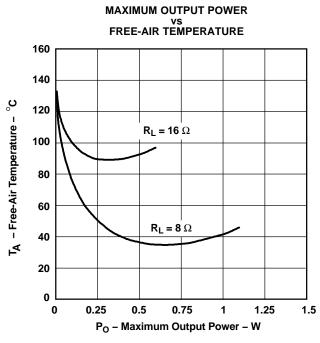
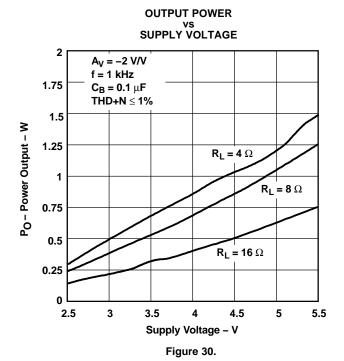
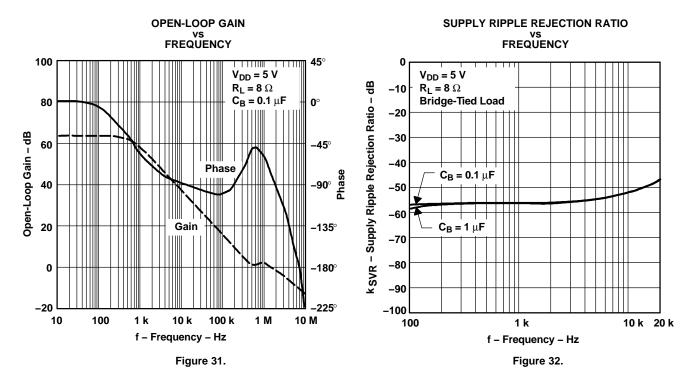


Figure 28.







SUPPLY RIPPLE REJECTION RATIO vs FREQUENCY 0 $V_{DD} = 5 V$ $R_L = 8 \Omega$ k SVR - Supply Ripple Rejection Ratio - dB -10 Single Ended $C_B = 0.1 \, \mu F$ -20 -30 -40 -50 $\textbf{C}_{\textbf{B}} = \textbf{1} \; \mu \textbf{F}$ -60 -70 -80 -90 -100100 1 k 10 k 20 k f - Frequency - Hz Figure 33.



APPLICATION INFORMATION

BRIDGED-TIED LOAD VERSUS SINGLE-ENDED MODE

Figure 34 shows a linear audio power amplifier (APA) in a bridge-tied load (BTL) configuration. A BTL amplifier actually consists of two linear amplifiers driving both ends of the load. There are several potential benefits to this differential drive configuration, but initially, let us consider power to the load. The differential drive to the speaker means that as one side is slewing up the other side is slewing down and vice versa. This, in effect, doubles the voltage swing on the load as compared to a ground-referenced load. Plugging twice the voltage into the power equation, where voltage is squared, yields 4 times the output power from the same supply rail and load impedance (see Equation 1).

$$V_{(rms)} = \frac{V_{O(PP)}}{2\sqrt{2}}$$

$$Power = \frac{V_{(rms)}^{2}}{R_{L}}$$
(1)

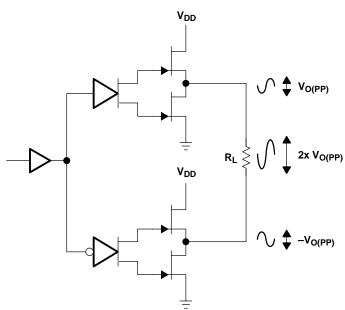


Figure 34. Bridge-Tied Load Configuration

In a typical computer sound channel operating at 5 V, bridging raises the power into an 8- Ω speaker from a singled-ended (SE) limit of 250 mW to 1 W. In sound power that is a 6-dB improvement, which is loudness that can be heard. In addition to increased power, frequency response is a concern; consider the single-supply SE configuration shown in Figure 35. A coupling capacitor is required to block the dc offset voltage from reaching the load. These capacitors can be quite large (approximately 40 μ F to 1000 μ F) so they tend to be expensive, occupy valuable PCB area, and have the additional drawback of limiting low-frequency performance of the system. This frequency-limiting effect is due to the high-pass filter network created with the speaker impedance and the coupling capacitance and is calculated with Equation 2.

$$f_{(corner)} = \frac{1}{2\pi R_L C_C}$$
 (2)

For example, a $68-\mu F$ capacitor with an $8-\Omega$ speaker would attenuate low frequencies below 293 Hz. The BTL configuration cancels the dc offsets, which eliminates the need for the blocking capacitors. Low-frequency performance is then limited only by the input network and speaker response. Cost and PCB space are also minimized by eliminating the bulky coupling capacitor.



APPLICATION INFORMATION (continued)

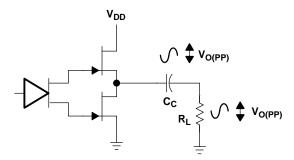


Figure 35. Single-Ended Configuration

Increasing power to the load does carry a penalty of increased internal power dissipation. The increased dissipation is understandable considering that the BTL configuration produces 4 times the output power of the SE configuration. Internal dissipation versus output power is discussed further in the *thermal considerations* section.

BTL AMPLIFIER EFFICIENCY

Linear amplifiers are notoriously inefficient. The primary cause of these inefficiencies is voltage drop across the output stage transistors. The internal voltage drop has two components. One is the headroom or dc voltage drop that varies inversely to output power. The second component is due to the sine-wave nature of the output. The total voltage drop can be calculated by subtracting the RMS value of the output voltage from V_{DD} . The internal voltage drop multiplied by the RMS value of the supply current, $I_{DD(RMS)}$, determines the internal power dissipation of the amplifier.

An easy-to-use equation to calculate efficiency starts out as being equal to the ratio of power from the power supply to the power delivered to the load. To accurately calculate the RMS values of power in the load and in the amplifier, the current and voltage waveform shapes must first be understood (see Figure 36).

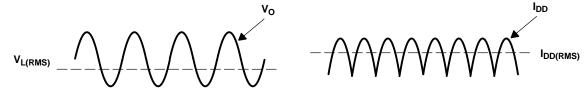


Figure 36. Voltage and Current Waveforms for BTL Amplifiers

Although the voltages and currents for SE and BTL are sinusoidal in the load, currents from the supply are different between SE and BTL configurations. In an SE application, the current waveform is a half-wave rectified shape, whereas in BTL it is a full-wave rectified waveform. This means RMS conversion factors are different. Keep in mind that for most of the waveform, both the push and pull transistor are not on at the same time, which supports the fact that each amplifier in the BTL device only draws current from the supply for half the waveform. The following equations are the basis for calculating amplifier efficiency.



APPLICATION INFORMATION (continued)

Efficiency =
$$\frac{P_L}{P_{SUP}}$$

Where:
$$P_L = \frac{V_L(RMS)}{R_L} = \frac{V_p^2}{2R_L}$$

$$V_{L(RMS)} = \frac{V_p}{\sqrt{2}}$$

$$P_{SUP} = V_{DD} I_{DD(RMS)} = \frac{V_{DD} 2V_p}{\pi R_L}$$

$$I_{DD(RMS)} = \frac{2V_p}{\pi R_L}$$

Efficiency of a BTL configuration = $\frac{\pi V_p}{2V_{DD}} = \frac{\pi \left(\frac{P_L R_L}{2}\right)^{1/2}}{2V_{DD}}$
e 1 employs Equation 4 to calculate efficiencies for four different output power levels. Note that the efficiency

Table 1 employs Equation 4 to calculate efficiencies for four different output power levels. Note that the efficiency of the amplifier is quite low for lower power levels and rises sharply as power to the load is increased, resulting in a nearly flat internal power dissipation over the normal operating range. Note that the internal dissipation at full output power is less than in the half power range. Calculating the efficiency for a specific system is the key to proper power supply design. For a stereo 1-W audio system with 8- Ω loads and a 5-V supply, the maximum draw on the power supply is almost 3.25 W.

Table 1. Efficiency Vs Output Power in 5-V 8- Ω BTL Systems

OUTPUT POWER (W)	EFFICIENCY (%)	PEAK-TO-PEAK VOLTAGE (V)	INTERNAL DISSIPATION (W)
0.25	31.4	2.00	0.55
0.50	44.4	2.83	0.62
1.00	62.8	4.00	0.59
1.25	70.2	4.47 ⁽¹⁾	0.53

⁽¹⁾ High peak voltages cause the THD to increase.

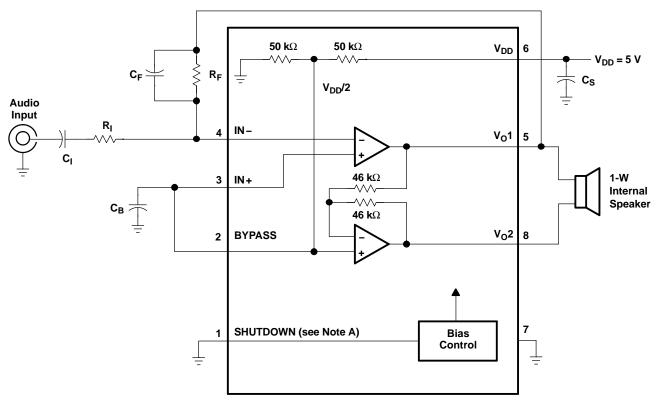
A final point to remember about linear amplifiers, whether they are SE or BTL configured, is how to manipulate the terms in the efficiency equation to utmost advantage when possible. Note that in Equation 4, V_{DD} is in the denominator. This indicates that as V_{DD} goes down, efficiency goes up.

For example, if the 5-V supply is replaced with a 10-V supply (TPA4861 has a maximum recommended V_{DD} of 5.5 V) in the calculations of Table 1, then efficiency at 1 W would fall to 31% and internal power dissipation would rise to 2.18 W from 0.59 W at 5 V. Then for a stereo 1-W system from a 10-V supply, the maximum draw would be almost 6.5 W. Choose the correct supply voltage and speaker impedance for the application.



SELECTION OF COMPONENTS

Figure 37 is a schematic diagram of a typical notebook computer application circuit.



NOTE A: SHUTDOWN must be held low for normal operation and asserted high for shutdown mode.

Figure 37. TPA4861 Typical Notebook Computer Application Circuit

Gain Setting Resistors, R_F and R_I

The gain for the TPA4861 is set by resistors R_F and R_I according to Equation 5.

$$Gain = -2\left(\frac{R_F}{R_I}\right) \tag{5}$$

BTL mode operation brings about the factor of 2 in the gain equation due to the inverting amplifier mirroring the voltage swing across the load. Given that the TPA4861 is a MOS amplifier, the input impedance is high; consequently, input leakage currents are not generally a concern, although noise in the circuit increases as the value of R_F increases. In addition, a certain range of R_F values are required for proper start-up operation of the amplifier. Taken together, it is recommended that the effective impedance seen by the inverting node of the amplifier be set between 5 k Ω and 20 k Ω . The effective impedance is calculated in Equation 6.

Effective Impedance =
$$\frac{R_F R_I}{R_F + R_I}$$
 (6)

As an example, consider an input resistance of 10 k Ω and a feedback resistor of 50 k Ω . The gain of the amplifier would be –10 V/V, and the effective impedance at the inverting terminal would be 8.3 k Ω , which is well within the recommended range.

For high-performance applications, metal film resistors are recommended because they tend to have lower noise levels than carbon resistors. For values of R_F above 50 $k\Omega$, the amplifier tends to become unstable due to a pole formed from R_F and the inherent input capacitance of the MOS input structure. For this reason, a small compensation capacitor of approximately 5 pF should be placed in parallel with R_F . This, in effect, creates a low-pass filter network with the cutoff frequency defined in Equation 7.



$$f_{\text{co(lowpass)}} = \frac{1}{2\pi R_{\text{F}} C_{\text{F}}}$$
 (7)

For example if R_F is 100 $k\Omega$ and C_F is 5 pF, then f_{co} is 318 kHz, which is well outside of the audio range.

Input Capacitor, C_I

In the typical application, an input capacitor, C_I , is required to allow the amplifier to bias the input signal to the proper dc level for optimum operation. In this case, C_I and R_I form a high-pass filter with the corner frequency determined in Equation 8.

$$f_{co(highpass)} = \frac{1}{2\pi R_{|}C_{|}}$$
 (8)

The value of C_l is important to consider, as it directly affects the bass (low-frequency) performance of the circuit. Consider the example where R_l is 10 k Ω and the specification calls for a flat bass response down to 40 Hz. Equation 8 is reconfigured as Equation 9.

$$C_{l} = \frac{1}{2\pi R_{l} f_{co}}$$
(9)

In this example, C_I is 0.40 μF ; so, one would likely choose a value in the range of 0.47 μF to 1 μF . A further consideration for this capacitor is the leakage path from the input source through the input network (R_I, C_I) and the feedback resistor (R_F) to the load. This leakage current creates a dc offset voltage at the input to the amplifier that reduces useful headroom, especially in high-gain applications. For this reason a low-leakage tantalum or ceramic capacitor is the best choice. When polarized capacitors are used, the positive side of the capacitor should face the amplifier input in most applications as the dc level there is held at $V_{DD}/2$, which is likely higher than the source dc level. Note that it is important to confirm the capacitor polarity in the application.

Power Supply Decoupling, C_S

The TPA4861 is a high-performance CMOS audio amplifier that requires adequate power supply decoupling to ensure that the output total harmonic distortion (THD) is as low as possible. Power supply decoupling also prevents oscillations for long lead lengths between the amplifier and the speaker. The optimum decoupling is achieved by using two capacitors of different types that target different types of noise on the power supply leads. For higher frequency transients, spikes, or digital hash on the line, a good low equivalent-series-resistance (ESR) ceramic capacitor, typically 0.1 μ F placed as close as possible to the device V_{DD} lead, works best. For filtering lower-frequency noise signals, a larger aluminum electrolytic capacitor of 10 μ F or greater placed near the power amplifier is recommended.

Midrail Bypass Capacitor, CB

The midrail bypass capacitor, C_B , serves several important functions. During start-up or recovery from shutdown mode, C_B determines the rate at which the amplifier starts up. This helps to push the start-up pop noise into the subaudible range (so slow it cannot be heard). The second function is to reduce noise produced by the power supply caused by coupling into the output drive signal. This noise is from the midrail generation circuit internal to the amplifier. The capacitor is fed from a 25-k Ω source inside the amplifier. To keep the start-up pop as low as possible, the relationship shown in Equation 10 should be maintained.

$$\frac{1}{\left(\mathsf{C}_{\mathsf{B}} \times 25 \,\mathsf{k}\Omega\right)} \le \frac{1}{\left(\mathsf{C}_{\mathsf{I}}\mathsf{R}_{\mathsf{I}}\right)} \tag{10}$$

As an example, consider a circuit where C_B is 0.1 μ F, C_I is 0.22 μ F and R_I is 10 $k\Omega$. Inserting these values into the Equation 10, we get 400 \leq 454 which satisfies the rule. Bypass capacitor, C_B , values of 0.1- μ F to 1- μ F ceramic or tantalum low-ESR capacitors are recommended for the best THD and noise performance.



SINGLE-ENDED OPERATION

Figure 38 is a schematic diagram of the recommended SE configuration. In SE mode configurations, the load should be driven from the primary amplifier output (V₀1, terminal 5).

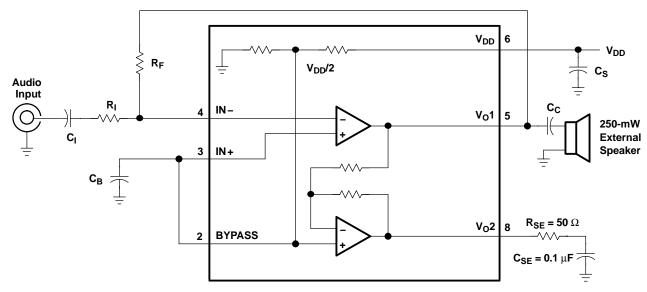


Figure 38. Singled-Ended Mode

Gain is set by the R_F and R_I resistors and is shown in Equation 11. Because the inverting amplifier is not used to mirror the voltage swing on the load, the factor of 2 is not included.

$$Gain = -\left(\frac{R_F}{R_I}\right) \tag{11}$$

The phase margin of the inverting amplifier into an open circuit is not adequate to ensure stability, so a termination load should be connected to V_O2 . This consists of a 50- Ω resistor in series with a 0.1- μ F capacitor to ground. It is important to avoid oscillation of the inverting output to minimize noise and power dissipation.

The output coupling capacitor required in single-supply SE mode also places additional constraints on the selection of other components in the amplifier circuit. The rules described earlier still hold with the addition of the following relationship:

$$\frac{1}{\left(\mathsf{C}_{\mathsf{B}}\times25\,\mathsf{k}\Omega\right)}\leq\frac{1}{\left(\mathsf{C}_{\mathsf{I}}\mathsf{R}_{\mathsf{I}}\right)}\ll\frac{1}{\mathsf{R}_{\mathsf{L}}\mathsf{C}_{\mathsf{C}}}\tag{12}$$

OUTPUT COUPLING CAPACITOR, Cc

In the typical single-supply SE configuration, an output coupling capacitor (C_C) is required to block the dc bias at the output of the amplifier thus preventing dc currents in the load. As with the input coupling capacitor, the output coupling capacitor and impedance of the load form a high-pass filter governed by Equation 13.

$$f_{\text{out high}} = \frac{1}{2\pi R_L C_C}$$
 (13)

The main disadvantage, from a performance standpoint, is that the load impedances are typically small, which drives the low-frequency corner higher. Large values of C_C are required to pass low frequencies into the load. Consider the example where a C_C of 68 μF is chosen and loads vary from 8 Ω , 32 Ω , and 47 $k\Omega$. Table 2 summarizes the frequency response characteristics of each configuration.



Table 2. Common Load Impedances vs Low-Frequence Output Characteristics in SE Mode
--

R _L	C _C	LOWEST FREQUENCY
8Ω	68 µF	293 Hz
32Ω	68 µF	73 Hz
47,000 Ω	68 μF	0.05 Hz

As Table 2 indicates, most of the bass response is attenuated into 8- Ω loads, while headphone response is adequate and drive into line level inputs (a home stereo for example) is good.

SHUTDOWN MODE

The TPA4861 employs a shutdown mode of operation designed to reduce supply current, $I_{DD(q)}$, to the absolute minimum level during periods of nonuse for battery-power conservation. For example, during device sleep modes or when other audio-drive currents are used (i.e., headphone mode), the speaker drive is not required. The SHUTDOWN input terminal should be held low during normal operation when the amplifier is in use. Pulling SHUTDOWN high causes the outputs to mute and the amplifier to enter a low-current state, $I_{DD(SD)} \sim 0.6 \ \mu A$. SHUTDOWN should never be left unconnected because amplifier operation would be unpredictable.

USING LOW-ESR CAPACITORS

Low-ESR capacitors are recommended throughout this applications section. A real capacitor can be modeled simply as a resistor in series with an ideal capacitor. The voltage drop across this resistor minimizes the beneficial effects of the capacitor in the circuit. The lower the equivalent value of this resistance, the more the real capacitor behaves like an ideal capacitor.

THERMAL CONSIDERATIONS

A prime consideration when designing an audio amplifier circuit is internal power dissipation in the device. The curve in Figure 39 provides an easy way to determine what output power can be expected out of the TPA4861 for a given system ambient temperature in designs using 5-V supplies. This curve assumes no forced airflow or additional heat sinking.

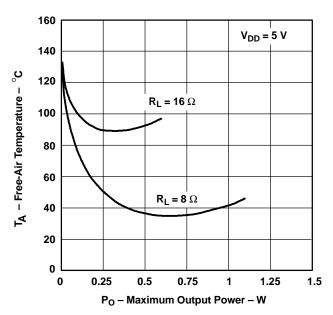


Figure 39. Free-Air Temperature vs Maximum Continuous Output Power



5-V VERSUS 3.3-V OPERATION

The TPA4861 was designed for operation over a supply range of 2.7 V to 5.5 V. This data sheet provides full specifications for 5-V and 3.3-V operation, as these are considered to be the two most common standard voltages. There are no special considerations for 3.3-V versus 5-V operation as far as supply bypassing, gain setting, or stability. Supply current is slightly reduced from 3.5 mA (typical) to 2.5 mA (typical). The most important consideration is that of output power. Each amplifier in TPA4861 can produce a maximum voltage swing of $V_{DD}-1$ V. This means, for 3.3-V operation, clipping starts to occur when $V_{O(PP)}=2.3$ V as opposed to when $V_{O(PP)}=4$ V while operating at 5 V. The reduced voltage swing subsequently reduces maximum output power into an 8- Ω load to less than 0.33 W before distortion begins to become significant.

Operation at 3.3-V supplies, as can be shown from the efficiency formula in Equation 4, consumes approximately two-thirds of the supply power for a given output-power level than operation from 5-V supplies. When the application demands less than 500 mW, 3.3-V operation should be strongly considered, especially in battery-powered applications.





7-Oct-2010

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Peak Temp ⁽³⁾	Samples (Requires Login)
TPA4861D	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	Contact TI Distributor or Sales Office
TPA4861DG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	Contact TI Distributor or Sales Office
TPA4861DR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	Request Free Samples
TPA4861DRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	Request Free Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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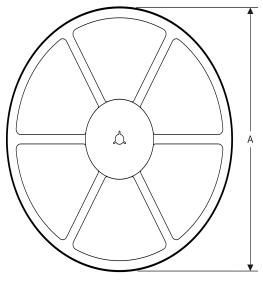
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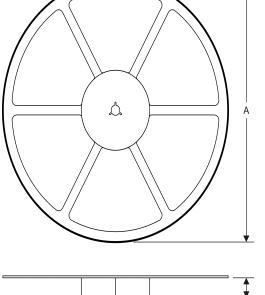
PACKAGE MATERIALS INFORMATION

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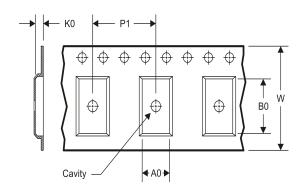
TAPE AND REEL INFORMATION

REEL DIMENSIONS





TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPA4861DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

PACKAGE MATERIALS INFORMATION

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPA4861DR	SOIC	D	8	2500	367.0	367.0	35.0

D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.



D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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